Ordering number: EN3035A

		NMOS LSI
	No.3035A	LM7006, 7006H
SANYO		Dual PLL Frequency Synthesizer Circuit
	L	Buut I BB Trequency Synthesizer Offcuit

Overview

The LM7006, 7006H is a PLL Frequency Synthesizer circuit for use in cordless telephones. It incorporates separate programmable dividers, phase comparators and dual-gain charge pumps for the transmit and receive sides. (Transmit side is operated by an independent power supply for standby function.) Device operation is controlled by a 40-bit serial input word, enabling simple control from a microcontroller by CCB.

The LM7006, 7006H is available in a 20-pin plastic DIP (300MIL). It operates from a single 4.0 to 5.5V supply.

Pin Assignment : DIP20S







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8090JN,TA/3249TA/2019YT,TS (US) No.3035-1/7

Equivalent Circuit Block Dia	gram			
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	TVpo			
han the stand of the		and the second		
				~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~
	Programmable Di 16bit (TX)	vider Phas	e Detector	
	L7	Unlor	ck Detector	
	L			
XIN (2)	Reference Divi	der if	$\mathbf{X} \in \mathbb{R}^{ }$.	<u> </u>
	N. 4 * * * * * * * * * * * * * * *			- 12 AOT
	la de la companya de La companya de la comp		· · · · · · · · · · · · · · · · · · ·	
		Char	se Pump //	
	Programmable (16bh (F	Divider Unio	ck Detector r//	
	rege ju		e in Align	
Vss (15)	$\phi_{1}\phi_{2} = \phi_{2}$		9 ia 🚸 🚝	
Back		Shift Barretar & Latab		<u> </u>
		40bit		AOR
				N. S.
		0		and the second
	CE CL	DI		
PIT : TX local OSC sign	al input	LDT : T	X unlock detection	n (open-drain)
(12.800MHz)	inar mput	PDT1 : T PDT2 · T	X Charge pump ou XCharge pump ou	itput (main)
PIR : RX local OSC sign	al input	AIT, AOT : T	X Tr for L.P.F am	p
V _{SS} : Ground	r than T V DD	LDR : R	X unlock detection	n (open-drain)
V _{BB} : Back gate bias pin		PDR2 : R	X Charge pump of	atput (main)
CE,CL,DI: Serial data input	· []	AIR,AOR : R	X Tr for L.P.F am	p
Absoluts Maximum Potings	ot ⊞o — 95°Ω ₩.	$\sim -0 M$		
Supply Voltage	V_{DD} max	RV_{DD},TV_{DD}	-0.3 to	0+6.0 V
Back Gate Bias	V _{BB} max	V _{BB}	-4.0 to	v - 2.0 V
Input Voltage	$V_{IN(1)}$ max $V_{IN(2)}$ max	OE,CL,DI,AIR,AI	$r = -0.3 t_{\rm e}$	0 + 7.0 V 0 + 0.3 V
Output Voltage	$V_{OUT(1)}$ max	AOR,AOT,LDR,LI	$\frac{100}{DT} = 0.0 \text{ to } \sqrt{D}$	0+7.0 V
Output Oursest	V _{OUT(2)} max	All other output pi	$ns = -0.3 \text{ to } V_D$	D + 0.3 V
Output Current	IOUT(1) max	AUR,AUT,LDR,LI	DT. () to 2.0 mA

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Back Gate Bias	V _{BB} max	VBB	-4.0
Input Voltage	V _{IN(1)} max	CE,CL,DI,AIR,AIT	0.3
	V _{IN(2)} max	All other input pins	-0.3 to V ₁
Output Voltage	V _{OUT(1)} max	AOR,AOT, <u>LDR</u> , <u>LDT</u>	-0.3
	V _{OUT(2)} max	All other output pins	-0.3 to V
Output Current	IOUT(1) max	AOR,AOT, LDR, LDT	
Allowable Power Dissipation	Pd max	Ta≦75°C	
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Allowable Power Dissipation	Pd max	Ta≦75°C	350	mW
Operating Temperature	Topr		-40 to $+75$	°C
Storage Temperature	Tstg		-55 to $+125$	°C

Note : Pins PIR and PIT are susceptible to damage by static discharge. Appropriate precautions should be taken during handling and operation.

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Allowable Operating Cor	ditions a	at Ta = -40	to +75	°C,V _{SS} =0V	min	typ n	nax	unit
Supply Voltage	VDD ·		D		4.U		0.0 E E	V
Input 'H'-Level Voltage	VIH	CE,CL,DI			Z.5		ວ.ວ ດີ້	V
Input 'L'-Level Voltage	V _{IL}	CE,CL,DI			U		U.5	V.
Output Voltage	VOUT	AOR,AOT, LDR,LDT			0		5.5	v
Input Frequency	$f_{IN(1)}$	XIN	Sine w	vave,	3.0 1	2.8 1	3.5	MH
			capaci	itive coupling				
			$V_{IN(1)}$	=50 mVrms				
	f _{IN(2)}	PIR,PIT	Sine w	vave,	200		400	MH:
			capaci	itive coupling				
			$V_{IN(2)}$	=70mVrms				
Input Voltage	$V_{IN(1)}$	XIN	Sine w	vave,	50	1	000 m	Vrm
	· · · ·		capaci	itive coupling				
			$f_{IN(1)}$ =	= 3.0 to 13.5MHz				
	$V_{1N(2)}$	PIR,PIT	Sine w	vave,	70		500 m	Vrms
		-	capaci	itive coupling				
			f _{IN(2)} =	=200 to 400MHz				
lectrical Characteristic	s under A	Allowable	Operat	ing Conditions	min	$_{ m typ}$	max	uni
Internal Feedback	$\mathbf{R}\mathbf{f}$	XIN PIR	,PIT			500		kΩ
Resistor								
Hysteresis Width	$\mathbf{V}\mathbf{h}$	CE,CL,D	I		0.1	0.5		V
Input 'H'-Level Current	$I_{IH(1)}$	CE,CL,D	01	$V_{l} = 5.5 V$			5.0	μA
-	$I_{IH(2)}$	XIN PIR	,PIT	$V_I = V_{DD}$			40	μA
	I _{IH(3)}	AIR, AIT		$V_{I} = 5.5V$		0.01	10.0	nA
Input 'L'-Level Current	ILLI	CE,CL,D	I	$V_I = V_{SS}$			5.0	μA
•	III.(2)	X _{IN} PIR.	PIT	$V_{I} = V_{SS}$			40	μA
	III.(3)	AIR AIT		$V_I = V_{SS}$		0.01	10.0	nA
Output 'H'-Level Voltage	е Vон	PDR1.PI	OR2	$I_0 = 0.1 \text{mA}$	0.6Vnn			۲
	0.11	PDT1 PI	DT2	-	20			
Output 'L'-Level Voltage	Volo	D PDR1 PI	DR2	$I_0 = 0.1 \text{mA}$			0.3	V
		PDT1.PI	DT2	~				
	Vore	DR.LD	T	$l_0 = 1.0 \text{mA}$			1.0	V
	Volg	AOR.AO	\mathbf{T}	$I_0 = 0.5 \text{mA}$			0.5	v
		,		AIR/AIT = 1.2V				
Output OFF-State	LOFF	1 LDR . LD	T	$V_0 = 5.5V$			5.0	цA
Leakage Current	IOFF	AOR.AO	T	$V_0 = 5.5V$			1.0	uA
	IOFF	3) PDR1.PI	DR2	$V_0 = 0.3 V. V_0 = 5.5 V$		0.01	10.0	nA
	-OFT(PDT1.PI	OT2	0				
Input Capacitance	CIN	XIN.PIR	PIT			2.5		DI
Supply Current	Inna	RVnn	,	※1		23	32	mA
······	$I_{DD(2)}$	$RV_{DD} +$	TV_{DD}	※2		45	62	mÆ
						,		
INT7006 and LM7006H D	uference	D17	.,	× 0 M. 0500	min	typ	max	uni
LM7006	DQI	$KV_{DD} + T$	V DD 3	$\times z$, Ta = 25°C			50	mA
LM7006H	IDD	$RV_{DD} + T$	V _{DD} >	% 2,Ta=25°C	50		55	mA
≈ 1 XIN = 12.8MHz,		· *	2 XIN	=12.8MHz,				
PIR = 400 MHz (70m	nVrms),		PIR:	=400MHz (70mVrms),				
other inputs : V _{SS} ,	-		PIT =	= 400MHz (70mVrms)				
outputs : open			othe	r inputs : V _{SS} ,				
			outp	uts : open				
			r					

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Note : The LM7006H is distinguished by an orange marking. I_{DD} is the only difference between the two devices.

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Pin Description

Pin Name	Pin No.	Input/Output	Description
XIN	2	Input	Reference OSC input 12.800MHz,50mVrms minimum (TCX0)
РІТ	14	Input	Transmit VCO input 200 to 400MHz,70mVrms minimum. Division ratio of transmit programmable divider is set by the TD0 to TD15 control bits to between 256 and 65535.
PIR	16	Input	Receive VCO input 200 to 400MHz,70mVrms minimum. Division ratio of receive programmable divider is set by the RD0 to RD15 control bits to between 256 and 65535.
RV _{DD}	17	-	Receive section power supply 4.0 to 5.5V to data shift register latch, reference divider, RX programmable divider, RX phase detector, RX unlock detector.
TVDD	13	- *1	Transmit section power supply 4.0 to 5.5V to TX programmable divider, TX phase detector, TX unlock detector.
V _{BB}	1	Output	Back gate bias pin Requires a 0.01µF capacitor between V _{BB} and ground.
V _{SS}	15	-	Ground
LDT LDR	87	Output N-channel Open drain	N-channel open-drain lock/unlock outputs for transmit and receive PLLs Lock : High-impedance Unlock : LOW The lock/unlock phase boundary is set by the UD0 to UD2 control bits. Extension of the phase difference signal is selected by the UE control flag.
PDT1 PDR1	9	Output (Tri-state)	Tri-state main charge pump outputs for transmit and receive PLLs Driven by the phase error signal obtained by comparing PLL frequency divided by N (fosc/N) with the reference frequency (fref) fosc/N > fref or leading: positive pulses fosc/N < fref or lagging: negative pulses fosc/N = fref: high-impedance
PDT2 PDR2	10 6	Output (Tri-state)	Tri-state auxiliary charge pump outputs for transmit and receive PLLs Driven by the PLLs phase error outputs only while PLL is out of lock, and high-impedance while PLL is in the lock range set by UD0 to UD2. Same polarity as main charge pump outputs.
AIT AOR	11 12	Input Ouptut	MOS N-channel transistor for TX PLL loop filter
AIR AOR	4 3	Input Output	MOS N-channel transistor for RX PLL loop filter
CE	18	Input ※2	Chip enable input A HIGH level enables serial data transfer into the LM7006.
CL	19	Input % 2	Serial input data clock
DI	20	Input %2	Serial data input

- *1 TV_{DD} Pin is connected to V_{SS} when transmit circuit is in power-off state (standby mode). For instance, connect resistor (47kΩ to 100kΩ) between TV_{DD} and V_{SS}.
 *2 High and Low input voltages on CE, CL, DI are held in the following range, respectively, regardless of the supply voltage (RV_{DD}). V_{IH}=2.5 to 5.5V, V_{IL}=0 to 0.5V

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Device Control



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No.	Data	Description	Associated data bits
(1)	TX Programmable Divider : TD0 to TD15	TD0 to TD15 form the TX side programmable divider ratio. TD0 is the least significant bit, and TD15 the most significant bit. The divider ratio must be between 256 and 65535, inclusive.	FR
(2)	RX Programmable Divider : RD0 to RD15	RD0 to RD15 form the RX side programmable divider ratio. RD0 is the least significant bit, and RD15 the most significant bit. The divider ratio must be between 256 and 65535, inclusive.	FR
(3)	UD0 UD1 UD2	UD0 to UD2 set the lock detector phase difference lock/unlock limit, as shown in the table below.	
	Unlock Detector Control : UE	$\frac{\text{UD2}}{\text{UD1}} \frac{\text{UD0}}{\text{UD0}} \frac{\text{Signal Name}}{\text{Signal Name}} \frac{\text{Detection Width}(\text{µsec})}{\text{Detection Width}(\text{µsec})}$ $\frac{0}{0} \frac{0}{0} \frac{1}{1} \frac{\text{ULD0}}{\text{ULD1}} \qquad $$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$	
(4)	Dead Zone Control : DZ	Selects the width of the phase comparator insensitive region. DZ=0:narrow DZ=1:wide	
(5)	Reference frequency Select : FR	FR=0: reference frequency=25.0kHz FR=1: reference frequency=12.5kHz	TD0 to TD15 RD0 to RD15
(6)	Device Test Flags : T0,T1	T0 and T1 are used to test the LM7006. They should both be set to "0" for normal operation.	

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The dual charge pump circuit ensures good performance during normal tracking and fast lock-in shown input frequency charges. During normal operation, only the main charge pump is employed to keep the PLL in sync. The auxiliary charge pump output is high-impedance. The loop filter time constant is relatively high, thus ensuring good sideband and modulation characteristics. When channels are changed, the PLL will lose lock and the auxiliary charge pump is activated. The filter resistor now consists of both R1S and R1M in parallel, reducing the filter time constant. PLL lock-in is thus accelerated.

Sample Application Circuit



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